Notice of Allowability	Application No.	Applicant(s)		
	09/662,682	LI ET AL.	\ ~	
	Examiner	Art Unit		
	Lan Vinh	1765		
	Lan viiii	1703		
The MAILING DATE of this communication apperall claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this a or other appropriate communicatio GHTS. This application is subject	pplication. If not included on will be mailed in due co	d ourse. THIS	
 This communication is responsive to <u>Applicants' s remarks</u> The allowed claim(s) is/are <u>1-21</u>. The drawings filed on <u>15 September 2000</u> are accepted by Acknowledgment is made of a claim for foreign priority un All b) ☐ Some* c) ☐ None of the: 	the Examiner.			
1. Certified copies of the priority documents have been received.				
2. Certified copies of the priority documents have been received in Application No.				
Copies of the certified copies of the priority doc International Bureau (PCT Rule 17.2(a)). * Certified copies not received:			on from the	
 Acknowledgment is made of a claim for domestic priority ur reference was included in the first sentence of the specifica (a) The translation of the foreign language provisional a 	tion or in an Application Data Shee	sional application) since a et. 37 CFR 1.78.	a specific	
6. Acknowledgment is made of a claim for domestic priority ur in the first sentence of the specification or in an Application	nder 35 U.S.C. §§ 120 and/or 121 s	since a specific reference	was included	
Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application. THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.				
 A SUBSTITUTE OATH OR DECLARATION must be submi INFORMAL PATENT APPLICATION (PTO-152) which give 	tted. Note the attached EXAMINEF is reason(s) why the oath or declar	R'S AMENDMENT or NO ration is deficient.	TICE OF	
 CORRECTED DRAWINGS (as "replacement sheets") mus (a) ☐ including changes required by the Notice of Draftspers 1) ☐ hereto or 2) ☐ to Paper No)-948) attached		
(b) \square including changes required by the proposed drawing co	orrection filed, which has b	een approved by the Exa	aminer.	
(c) \square including changes required by the attached Examiner's	Amendment / Comment or in the	Office action of Paper No)	
ldentifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the	84(c)) should be written on the draw ne margin according to 37 CFR 1.121	ings in the front (not the b	ack) of	
 DEPOSIT OF and/or INFORMATION about the depose attached Examiner's comment regarding REQUIREMENT FOR TI 	SIT OF BIOLOGICAL MATERIAL HE DEPOSIT OF BIOLOGICAL MA	must be submitted. No ATERIAL.	ote the	
Attachment(s)				
1□ Notice of References Cited (PTO-892)	5∭ Notice of Informal P	atent Application (PTO-1	52)	
2☐ Notice of Draftperson's Patent Drawing Review (PTO-948)		6☐ Interview Summary (PTO-413), Paper No		
3 Information Disclosure Statements (PTO-1449 or PTO/SB/08) Paper No),	nent/Comment		
4 Examiner's Comment Regarding Requirement for Deposit of Biological Material	8⊠ Examiner's Stateme 9⊡ Other	ent of Reasons for Allowa	nce	
		Lan Vinh AU 1765	/	

Application/Control Number: 09/662,682

Art Unit: 1765

Allowable Subject Matter

Claims 1-21 are allowed.

The following is an examiner's statement of reasons for allowance:

Regarding claims 1, 11, 21, the applicants have presented a persuasive argument that the cited prior art of record fails to disclose a method for producing porous silicon comprising the step of forming the porous silicon by etching the Si surface having a thin discontinuous layer of metal in a HF and oxidant solution / etching the Si surface having a thin discontinuous layer of metal in a HF and oxidant solution for a period of about two seconds up to 60 minutes, said etching being conducted without external electrical bias. The closest cited prior art of Lee et al (US 5,565,084) discloses an electropolishing method comprises the step of etching the porous Si surface having a thin layer of metal in a HF and oxidant solution while breaking the supply of the electricity/without external electrical bias for 1 minute after the step of forming the porous silicon by conducted an etching step with supplied electric current (col 4, lines 30-42)

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

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1-

Conclusion

2. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lan Vinh whose telephone number is 571 272 1471. The examiner can normally be reached on M-F 8:30-5:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 571 272 1465. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703 308-0661.

IM

January 2, 2004